

FDR6674A

30V N-Channel PowerTrench® MOSFET

General Description

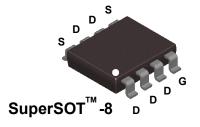
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{\text{DS(ON)}}$ in a small package.

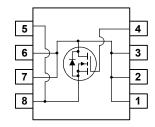
Applications

- · Synchronous rectifier
- DC/DC converter

Features

- 11.5 A, 30 V. $R_{DS(ON)} = 9.5 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 8.5 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- High power and current handling capability in a smaller footprint than SO8





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	11.5	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	1.8	W
		(Note 1b)	1.0	
		(Note 1c)	0.9	
T _J , T _{STG}	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	70	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	20	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
.6674A	FDR6674A	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1				I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate–Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -12 V , V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.8	1.2	2	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 10.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 10.5 \text{ A}, T_J 125^{\circ}\text{C}$ $V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}$		8.2 11.5 6.8	9.5 16 8	mΩ
I _{D(on)}	On-State Drain Current	V _{GS} = 4.5 V, V _{DS} = 5 V	50			Α
g FS	Forward Transconductance	V _{DS} = 10 V, I _D = 11.5 A		75		S
Dynamic	: Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, \ V_{GS} = 0 \text{ V},$		5070		pF
Coss	Output Capacitance	f = 1.0 MHz		550		pF
C _{rss}	Reverse Transfer Capacitance			230		pF
Switchin	g Characteristics (Note 2)		•	•	•	•
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		17	25	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		18	25	ns
t _{d(off)}	Turn-Off Delay Time			69	100	ns
t _f	Turn-Off Fall Time	1		29	42	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 11.5 \text{ A},$		33	46	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5V		7.5		nC
Q_{gd}	Gate-Drain Charge	1		6.8		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain–Source				2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.7	1.2	V

Notes:

^{1.} R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 70°/W when mounted on a 1in² pad of 2 oz copper



b) 125°/W when mounted on a .04 in² pad of 2 oz copper



c) 135°/W when mounted on a minimum pad.



2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

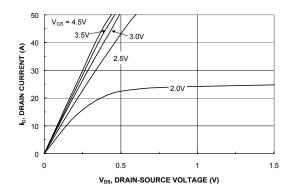
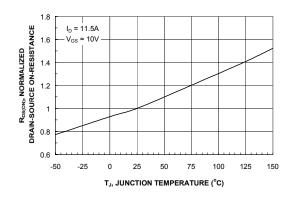


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



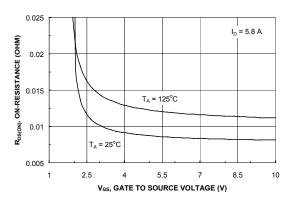
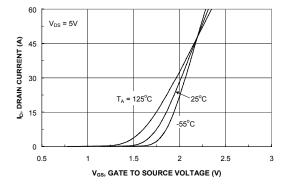


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



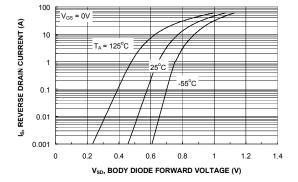
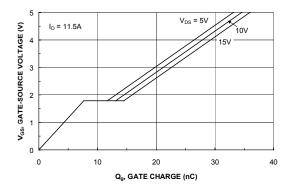


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



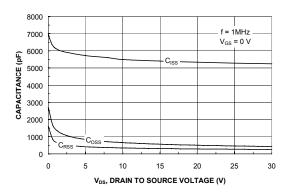
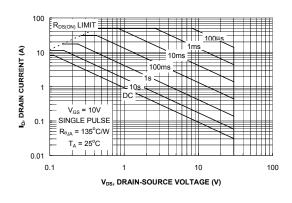


Figure 7. Gate Charge Characteristics.





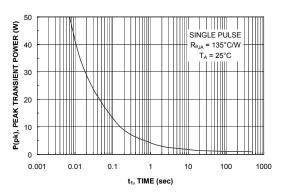


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

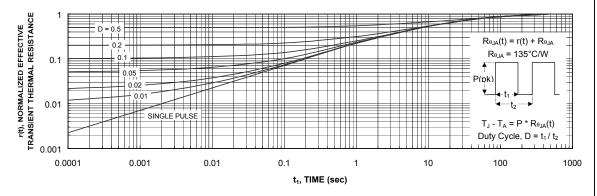
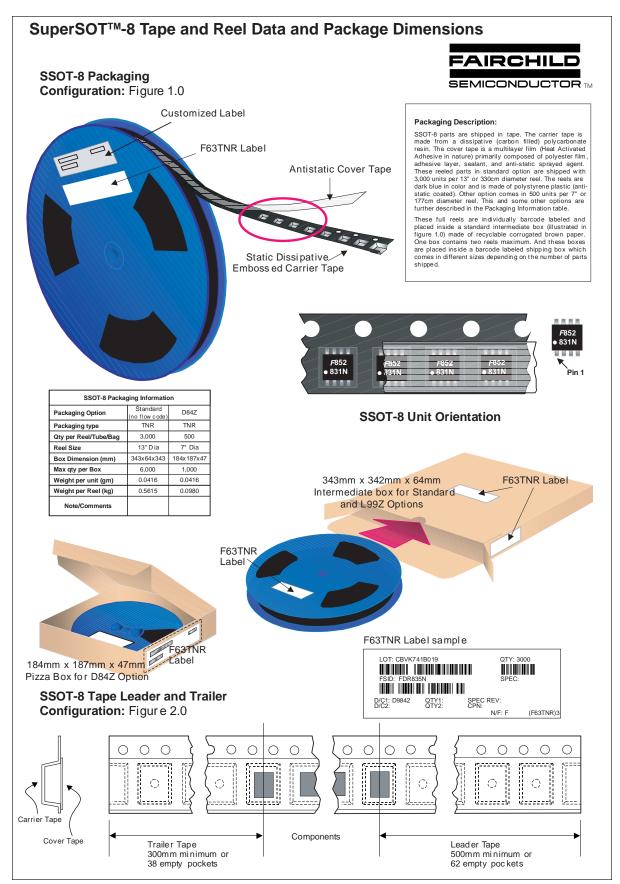
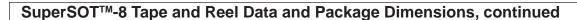


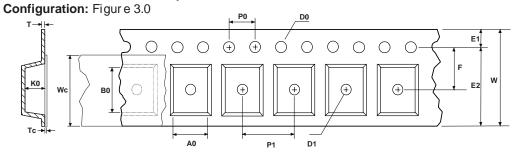
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





SSOT-8 Embossed Carrier Tape



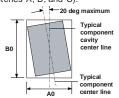


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SSOT-8 (12mm)	4.47 +/-0.10	5.00 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.280 +/-0.150	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

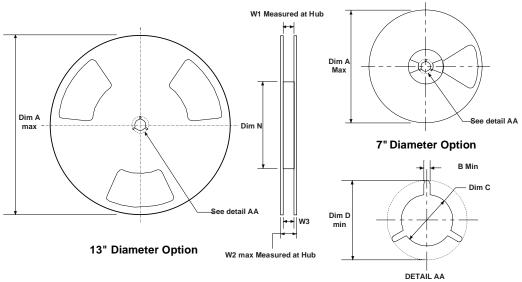


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

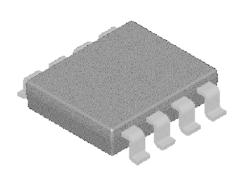
SSOT-8 Reel Configuration: Figur e 4.0

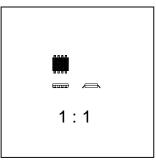


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

SuperSOT™-8 (FS PKG Code 34, 35)

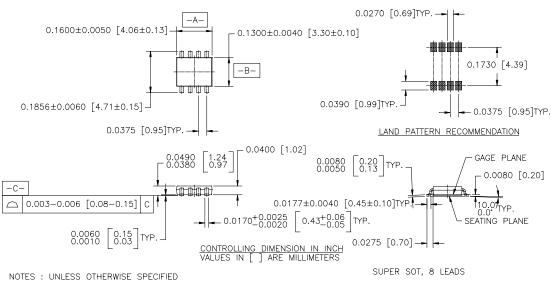




Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0416



STANDARD LEAD FINISH TI BE 200 MICROINCHES / 5.08 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.

2. NO JEDEC REGISTRATION AS JAN. 1996

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